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Triplet-blockaded Josephson supercurrent in double quantum dots

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Serial double quantum dots created in semiconductor nanostructures provide a versatile platform for investigating two-electron spin quantum states, which can be tuned by electrostatic gating and an external magnetic field. In this Rapid Communication, we directly measure the supercurrent reversal between adjacent charge states of an InAs nanowire double quantum dot with superconducting leads, in good agreement with theoretical models. In the even charge parity sector, we observe a supercurrent blockade with increasing magnetic field, corresponding to the spin singlet to triplet transition. Our results demonstrate a direct spin to supercurrent conversion, the superconducting equivalent of the Pauli spin blockade. This effect can be exploited in hybrid quantum architectures coupling the quantum states of spin systems and superconducting circuits.

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Semiconductor quantum dots, where the orbital and spin states of single localized electrons can be controlled [1], are one of the leading platforms for quantum information processing [2]. Specifically, double quantum dots (DQDs) connected in a series [3] became the preferred physical implementation of spin [4], and spin-orbit quantum bits [5] in low-dimensional semiconductor nanodevices, such as heterostructures hosting a two-dimensional electron gas or semiconductor nanowires. In these devices, the readout of the spin quantum state relies on spin-dependent single electron tunneling processes, which then enable charge readout via direct electronic transport [1], charge sensing techniques [6], or dipole coupling to a microwave resonator [7,8].

In a superconducting nanodevice, the dissipationless supercurrent $I_S$ at zero voltage bias is driven by the quantum mechanical phase difference $\phi$ up to a maximum amplitude, $I_C$, the critical current [9]. In the lowest order of tunneling, the supercurrent-phase relationship (CPR) [10] is sinusoidal, $I_S(\phi) = I_C \sin(\phi)$, which describes the coherent transfer of single Cooper pairs through the weak link. When the weak link is a nonmagnetic tunnel barrier, a zero phase difference is energetically favorable in the absence of supercurrent, which is described by a positive critical current, $I_C > 0$. In contrast, a negative coupling yields a supercurrent reversal, $I_C < 0$, often denoted a $\pi$ junction due the $\pi$ phase shift in the CPR. This negative coupling has been observed in ferromagnetic weak links [11,12], out-of-equilibrium electron systems [13], and semiconductor quantum dot junctions [14,15].

The dependence of the critical current on the spin state and charge state of a DQD has also been addressed theoretically [16–22], and the recent progress in materials science of superconductor-semiconductor hybrid nanostructures [23] enabled measurements of the amplitude of the critical current as well [24,25], in correlation with the charge states of the DQD.

In this Rapid Communication, we report on direct measurements of the CPR through a DQD weak link formed by an electrostatically gated InAs nanowire. By employing a phase-sensitive measurement scheme, where the DQD is embedded in a superconducting quantum interference device (SQUID), we characterize the full CPR of the DQD, enabling a signifful measurement of $I_C$. The direct observation of the supercurrent reversal in the total charge number boundaries allowed us to identify the even and odd occupied states. Finally, the magnetic field dependence of the supercurrent amplitude in the even occupied state reveals the presence of a supercurrent blockade in the spin-triplet ground state, in agreement with numerical calculations.

We built our device (Fig. 1) from an approximately 7-μm-long InAs nanowire grown by molecular beam epitaxy, and in situ partially covered by a 6-nm-thick epitaxial aluminum shell with a typical superconducting gap of $\Delta \approx 200 \mu$eV [23,26]. We formed two segments with the aluminum layer

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FIG. 1. Device layout and characterization. (a) Color-enhanced electron micrograph of the nanowire DQD junction with five wrap-around gates (yellow) which provide the confining potential. The $V_{BL}$, $V_C$, and $V_{BR}$ gate voltages define the barriers, while $V_L$ and $V_R$ control the number of electrons on the dots. The aluminum shell (blue) is selectively etched away in the weak link section (green denotes bare InAs). The scale bar denotes 100 nm. (b) Perspective drawing of the DQD junction highlighting the conformal gates. (c) Color-enhanced electron micrograph of the DQD junction with five wrap-around gates (yellow) which provide the confining potential. The atomic layer deposition. Finally, 40-nm-wide and 50-nm-thick Ti/Au gates [in yellow in Fig. 1(a)] were evaporated under three angles to ensure a conformal coverage around the wire [schematically shown in Fig. 1(b)]. Five gates defined the DQD (on the right) and a single gate controlled the reference arm [on the left in Fig. 1(c)]. Details on the device fabrication are shown in the Supplemental Material [27]. All of our measurements were performed in a dilution refrigerator with a base temperature of approximately 30 mK.

We first characterize the DQD with the leads driven to the normal state by a large magnetic field, $B_{L} = 0.5$ T. We measure the differential conductance $dI/dV$ of the DQD with the reference arm fully depleted [Fig. 1(d)]. We control the coupling to the leads with the gate voltages $V_{BL}$ and $V_{BR}$, and the interdot coupling is tuned by $V_C$ [Fig. 1(a)]. A characteristic honeycomb diagram is plotted in Fig. 1(f), where the charge occupancy of the dots ($n_L$, $n_R$) is set by the voltages applied on the two plunger gates, $V_L$ and $V_R$.

We perform the CPR measurements with the leads being superconducting and with the reference arm of the SQUID opened with its electrostatic gate so that it exhibits a higher critical current than the DQD arm. Due to this asymmetry, the phase drop over the DQD junction is determined by the magnetic flux $\Phi$ through the SQUID loop area [Fig. 1(e)] [14,28], which is proportional to the applied magnetic field $B_L$. We measure the switching current $I_{SW}$ of the SQUID by ramping a current bias in a sawtooth wave form and recording the bias current value when the junction switches to the resistive state marked by a threshold voltage drop of the order of 10 μV. We show a typical data set in Fig. 1(g), where each pixel in the main panel is an average of 18 measurements. The right side panel shows the raw data points at two plunger gate settings denoted by the magenta and green lines in the main panel, as well as the fitted sinusoidal curves in the following functional

$$I_{SW} = I_{0} \sin \left( \frac{2\pi \Phi}{\Phi_0} \right)$$

where $I_{0}$ is the amplitude of the oscillation, $\Phi_0$ is the flux quantum, and $\Phi$ is the magnetic flux through the SQUID loop.
We understand these data using a two-orbital Anderson model, where each dot with an on-site charging energy $U_i$ hosts a single spinful level at $e_i$ with the dot index $i = L, R$. In the experiment, this corresponds to a quantum dot orbital level spacing which is larger than the charging energy $[14]$. We consider an interdot charging energy term $U_{C}n_{l}n_{R}$ and an effective interdot tunneling amplitude $I_{C}$. The tunnel coupling energies to the superconducting leads are denoted by $\Gamma_{l,R}$.

We consider the leading term of the supercurrent in the weak-coupling limit where $I_{C}, \Gamma_{l}, \Gamma_{R} \ll \Delta \ll U_{i}$, $[18,30]$, and evaluate the current operator $I(\phi) = i\hat{I} \{H, \hat{n}_{g}\}$, where $H$ is the Hamiltonian of the system at a phase difference of $\phi$ between the superconducting leads (see the Supplemental Material $[27]$). We numerically evaluate $\langle I(\phi) \rangle = I_{C} \sin \phi$ to find the signful $I_{C}$. We perform a global fit of the calculated sign reversal contours $[\text{see the dashed lines in Fig. 2(a)}]$ against the experimental data set and recover $U_{L} = 596.6 \mu$eV, $U_{R} = 465.9 \mu$eV, $U_{C} = 41.5 \mu$eV, and $I_{C} = 85 \mu$eV. We match the critical current amplitude scale with the experimental data by setting $\Gamma_{L} = \Gamma_{R} = 33.2 \mu$eV. The width of the even-odd transitions establishes an upper bound on the electron temperature of the DQD, $T < 80$ mK. We use these parameters to display $I_{C}(V_{L}, V_{R})$ in Fig. 2(b) and find a good correspondence with the experimental data using a zero bandwidth (ZBW) approximation $[25,31]$ (see the Supplemental Material $[27]$).

The observed supercurrent reversal $[14,32]$ is linked to the number of permutations of fermion operators required to transfer a spin-singlet Cooper pair through the DQD (see the Supplemental Material $[27]$). In the weak-coupling limit, this amounts to counting the number of same-spin dot electrons, which each electron in the Cooper pair crosses. Each such crossing contributes with a factor of $-1$ to $I_{C}$, which we illustrate for a DQD with even $[\text{Fig. 2(c)}]$ and odd charge occupations $[\text{Fig. 2(d)}]$. Consequently, the sign of $I_{C}$ is determined by the ground-state charge parity of the DQD.

Next, we focus on the magnetic field dependence of $I_{DQD}$ $[\text{Fig. 3(a)}]$ along the total energy axis $[\text{solid line in Fig. 2(a)}]$ spanning both even and odd charge states. At $B_{z} = 0$, a finite $I_{C}$ results in a singlet-triplet splitting $\Delta_{ST}$ in the even occupied $(1,1)$ charge state $[1]$. We model the DQD with an effective identical $g$-factor on both dots, which results in a spin-polarized triplet ground state above a threshold magnetic field, $B_{ST} = \Delta_{ST} / (g^{*} \mu_{B})$. To account for spin-orbit coupling, we refine our interdot tunneling Hamiltonian to include both spin-conserving and spin-flip tunneling amplitudes $t_{0}$ and $t_{l}$, resulting in an effective $I_{C} = \sqrt{t_{0}^{2} + t_{l}^{2}}$ (see the Supplemental Material $[27]$).

With a global fit to the experimental data $[\text{Figs. 3(a) and 3(b)}]$, we extract $t_{0} = 80 \mu$eV, $t_{l} = 30 \mu$eV, and $g^{*} = 15.9$. This $g$-factor is in agreement with earlier experimental values measured on InAs quantum dots $[5,33–35]$ and ballistic channels with superconducting leads $[26,36]$. We estimate the spin-orbit length $l_{SO} = I_{dot} / (2\sqrt{|t_{l}|}) \approx 75$ nm $[37]$, using the gate pitch as an estimate of the dot length, $l_{dot} \approx 40$ nm. This coupling length yields an energy scale $E_{SO} = \hbar / (2m^{*}l_{SO}^{2}) = 290 \mu$eV with an effective electron mass of $m^{*} = 0.023m_{e}$, which is similar to earlier experimental results on semiconductor nanowires in the presence of strong electrostatic confinement $[38,39]$.

\begin{equation}
I_{SW} = I_{ref} + I_{DQD} \sin \phi,\end{equation}

where $\phi = 2\pi(B_{y} - B_{o}) / B_{o}$, with $B_{o} \approx 1.7$ mT being the magnetic field periodicity corresponding to a flux change equal to the superconducting flux quantum $\phi_{0} = h / 2e$ and $B_{o}$ being the offset perpendicular magnetic field. The switching current values $I_{ref}$ and $I_{DQD}$ represent the reference arm and the DQD junction contributions, respectively. We show these fitted values as a function of the gate voltage $V_{L}$ in the lower subpanel of Fig. 1(g), which displays the sign change of $I_{DQD}$ at the charge state boundaries. We note that the change in the environmental impedance $[29]$ causes a slight modulation of $I_{ref}$ as well, despite the lack of any capacitive coupling between the two weak links. However, in our measurements $I_{ref} > 5|I_{DQD}|$ is always fulfilled, enabling a reliable observation of the supercurrent reversal in the DQD.

In Fig. 2(a), we plot $I_{DQD}$ as a function of the plunger gate voltages $V_{L}$ and $V_{R}$ resulting in the zero magnetic field charge-stability diagram of the DQD mapped by the supercurrent. Remarkably, our phase-sensitive measurement directly shows that the supercurrent reversal is associated with the change in the total charge number, and it is absent in the case of internal charge transfers with $(n_{L}, n_{R}) \rightarrow (n_{L} \pm 1, n_{R} \pm 1)$. However, $|I_{DQD}|$ exhibits maxima near all charge boundaries, consistently with earlier experiments $[25]$.

\begin{figure}[h]
\centering
\includegraphics[width=\textwidth]{figure2.png}
\caption{The supercurrent charge-stability diagram at zero magnetic field. (a) Color map of the measured $I_{DQD}$ as a function of the plunger gate voltages $V_{L}$ and $V_{R}$ revealing a supercurrent sign reversal between the adjacent total charge sectors. The dashed lines denote the numerically calculated charge boundaries (see the text). Measurements along the solid line are shown in Figs. 1(g) and 3(a). (b) The ZBW calculation of the critical current $I_{C}$ of the DQD using the same parameters. The charge occupation of the dots is indicated in parentheses. Visual representations of a Cooper pair transfer when the DQD has an (c) even and (d) odd charge occupation. The $\pm 1$ values indicate the spin permutation parity for each spin species, which yields a supercurrent reversal for an odd charge occupation of the DQD (see the text).}
\end{figure}
In Fig. 3(c), we plot the calculated expectation value \( \langle S_Z \rangle \) of the total spin \( Z \) component of the DQD, which visualizes the transition between the spin-singlet state \( \langle S_Z \rangle = 0 \) and the spin-polarized triplet state, where \( \langle S_Z \rangle = 1 \), as a function of the magnetic field. This transition point at \( B_{ST} \) is accompanied by a drop of the critical current in the \((1,1)\) sector, however, this sudden decrease is absent in the odd sector [see the blue regions in Fig. 3(b)]. We note that the gradual global decrease in \( I_{DQD} \) is consistent with the orbital effect of the magnetic field applied along the nanowire [40].

We analyze these data in Fig. 4, where we first find the charge state boundary at each value of \( B_i \) at \( I_{DQD} = 0 \) [blue dots and error bars in Fig. 4(a)] and overlay the calculated boundary [black solid line, corresponding to Fig. 3(b)]. We quantify \( B_{ST} \approx 80 \text{ mT} \), which agrees consistently with the characteristic cutoff magnetic field of \( I_{DQD} \) at several plunger gate values [dots in Fig. 4(b), colors corresponding to the arrows in Fig. 3(a)]. However, we observe a deviation between the calculated and measured charge boundary near \( B_{ST} \), which may stem from the microscopic details of the spin-orbit coupling that our model does not account for. We find an agreement between the calculated critical current \( I_c(B) \) [solid lines in Fig. 4(b)] with a common scaling factor of 0.29, which may be the result of the reduced switching current inside the charge state due to thermal activation compared to the corresponding critical current [29].

The suppression of the Josephson supercurrent through a DQD in the spin-triplet sector can be understood considering the virtual states involved in the Cooper pair transfer. Starting from the \((1,1)\) \( T_{\uparrow \downarrow} \) state close to the charge boundary with the single occupation sector, we always encounter a virtual state with a double occupation on one of the dots [magenta circle in Fig. 4(c)]. In the \( U \gg \Delta \) limit corresponding to our experiments, this configuration is energetically unfavorable and suppresses Cooper pair tunneling. In contrast, a spin-singlet starting condition can avoid this configuration [Fig. 4(d)]. We finally note that the opposite limit, where \( U \ll \Delta \), also leads to a triplet supercurrent blockade [20] (see the Supplemental Material [27]), which persists with a finite residual supercurrent in the spin-triplet state when \( U \sim \Delta \).

In conclusion, we directly measured the supercurrent reversal associated with the even-odd charge occupation in an InAs DQD, where the large level spacing allows us to use a single orbital for each dot in our quantitative modeling. In the \((1,1)\) charge sector, we showed that the singlet to triplet transition is accompanied by a supercurrent blockade. This enables a direct spin to supercurrent conversion [36,41] in

FIG. 4. Triplet-blockaded supercurrent. (a) The measured (blue dots and error bars) and calculated (black solid line) even-odd charge boundary extracted from Figs. 3(a) and 3(b). (b) Dots: The measured \( I_{DQD} \) at three plunger gate settings in the even \((1,1)\) sector [see the corresponding arrows in Fig. 3(a)]. Scaled theoretical values are shown as solid lines (see the text). Representative sixth-order tunneling processes are shown (c) in the \( T_{\uparrow \downarrow} \) and (d) in the singlet regime. The white arrows denote an initial occupied electron state including the spin. The gray arrows visualize the final state for each numbered process.

Raw data sets and computer code are available at the Zenodo repository [42].

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